Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

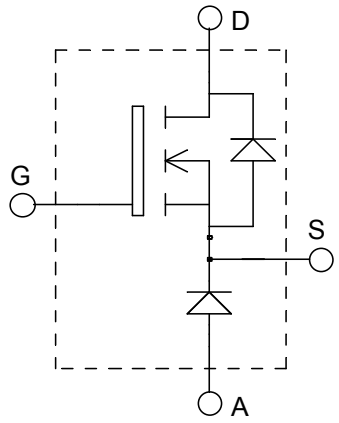
Contact us

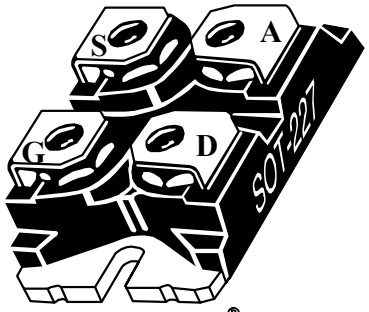
Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

APT20M120JCU3

ISOTOP® Buck chopper MOSFET + SiC chopper diode Power module

V_{DSS} = 1200V
R_{DSon} = 560mΩ typ @ Tj = 25°C
I_D = 20A @ Tc = 25°C





ISOTOP®

Application

- AC and DC motor control
- Switched Mode Power Supplies

Features

- ***Power MOS 8™ MOSFET***
  - Low R_{DSon}
  - Low input and Miller capacitance
  - Low gate charge
  - Avalanche energy rated
- ***SiC Schottky Diode***
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature Independent switching behavior
  - Positive temperature coefficient on VF
- ISOTOP® Package (SOT-227)
- Very low stray inductance
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- RoHS Compliant

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{DSS}	Drain - Source Breakdown Voltage		1200	V
I_D	Continuous Drain Current	T_c = 25°C	20	A
		T_c = 80°C	15	
I_{DM}	Pulsed Drain current		104	
V_{GS}	Gate - Source Voltage		±30	V
R_{DSon}	Drain - Source ON Resistance		672	mΩ
P_D	Maximum Power Dissipation	T_c = 25°C	543	W
I_{AR}	Avalanche current (repetitive and non repetitive)		14	A

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} =1200V V_{GS} = 0V	T_j = 25°C			100	µA
			T_j = 125°C			500	
$R_{DS(on)}$	Drain – Source on Resistance	V_{GS} = 10V, I_D = 14A			560	672	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 2.5mA		3	4	5	V
I_{GSS}	Gate – Source Leakage Current	V_{GS} = ±30 V				±100	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*	*Min*	*Typ*	*Max*	*Unit*
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1MHz		7736		pF
C_{oss}	Output Capacitance			715		
C_{rss}	Reverse Transfer Capacitance			92		
Q_g	Total gate Charge	V_{GS} = 10V V_{Bus} = 600V I_D = 14A		300		nC
Q_{gs}	Gate – Source Charge			50		
Q_{gd}	Gate – Drain Charge			140		
$T_{d(on)}$	Turn-on Delay Time	**Resistive switching @ 25°C** V_{GS} = 15V V_{Bus} = 800V I_D = 14A R_G = 2.2Ω		50		ns
T_r	Rise Time			31		
$T_{d(off)}$	Turn-off Delay Time			170		
T_f	Fall Time			48		

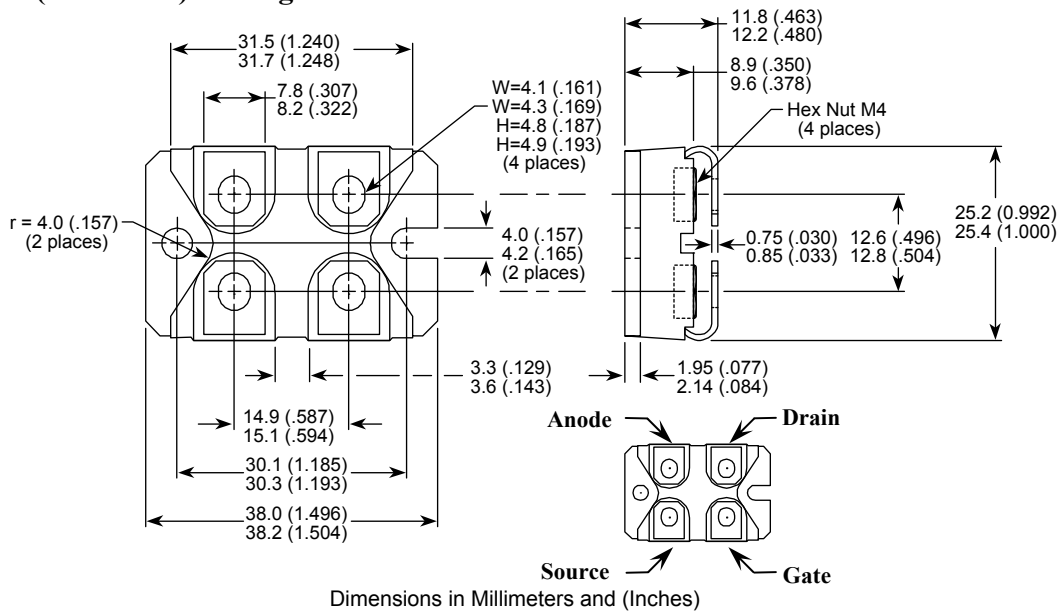
SiC chopper diode ratings and characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Reverse Leakage Current	V_R=1200V	T_j = 25°C		32	200	µA
			T_j = 175°C		56	1000	
I_F	DC Forward Current		Tc = 100°C		10		A
V_F	Diode Forward Voltage	I_F = 10A	T_j = 25°C		1.6	1.8	V
			T_j = 175°C		2.3	3	
Q_C	Total Capacitive Charge	I_F = 10A, V_R = 600V di/dt =500A/µs			80		nC
C	Total Capacitance	f = 1MHz, V_R = 200V			96		pF
		f = 1MHz, V_R = 400V			69		

Thermal and package characteristics

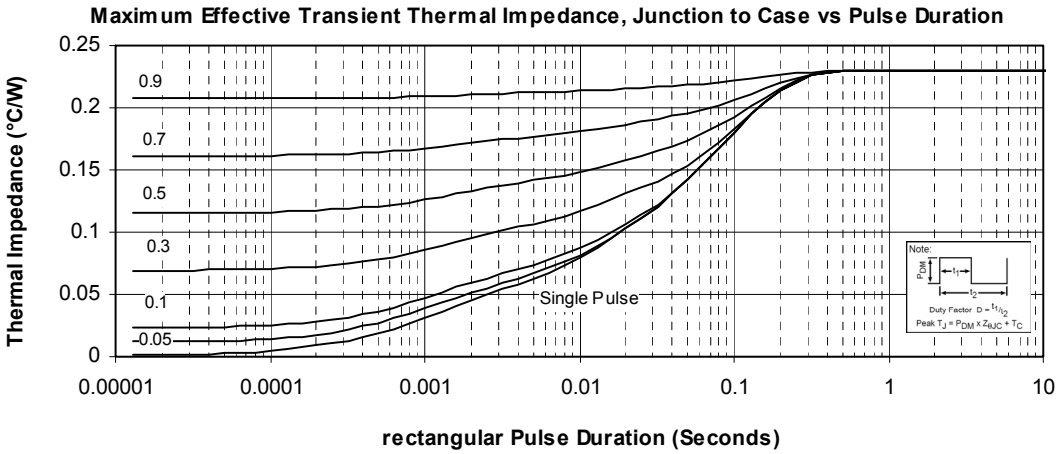
Symbol	*Characteristic*		*Min*	*Typ*	*Max*	*Unit*
R_{thJC}	Junction to Case Thermal Resistance	Mosfet			0.23	°C/W
		SiC Diode			1.65	
R_{thJA}	Junction to Ambient (IGBT & Diode)				20	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz		2500			V
T_J,T_{STG}	Storage Temperature Range		-40		150	°C
T_L	Max Lead Temp for Soldering:0.063" from case for 10 sec				300	
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)				1.5	N.m
Wt	Package Weight			29.2		g

SOT-227 (ISOTOP®) Package Outline

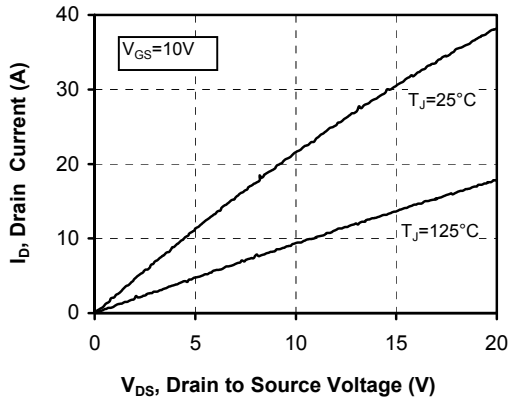


Dimensions in Millimeters and (Inches)

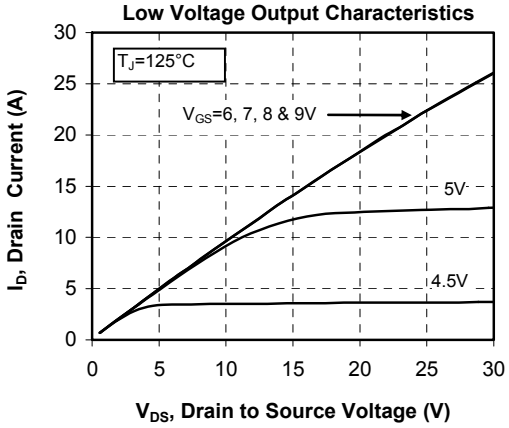
Typical Mosfet Performance Curve



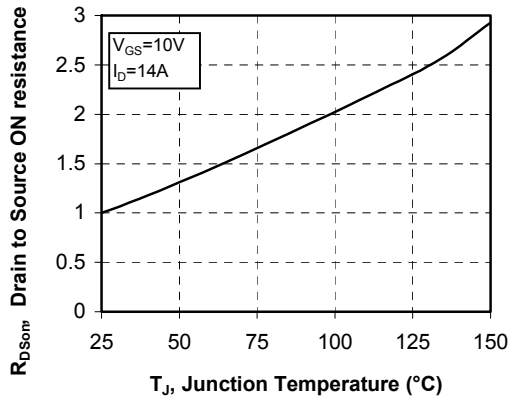
Low Voltage Output Characteristics



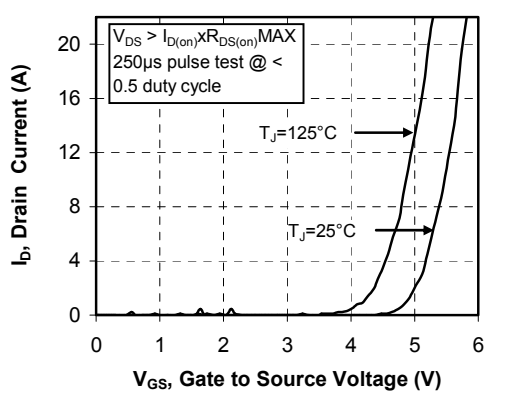
Low Voltage Output Characteristics



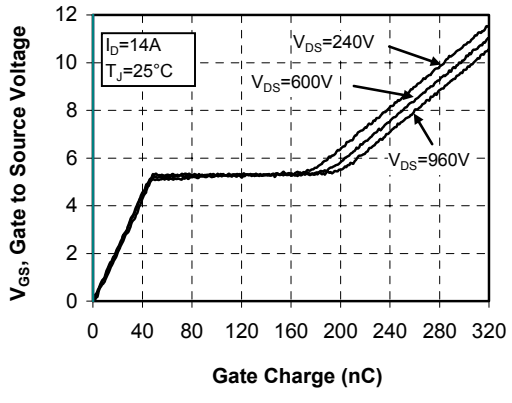
Normalized $R_{DS(on)}$ vs. Temperature



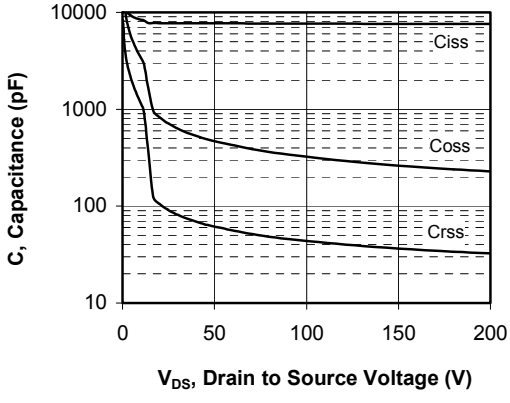
Transfert Characteristics



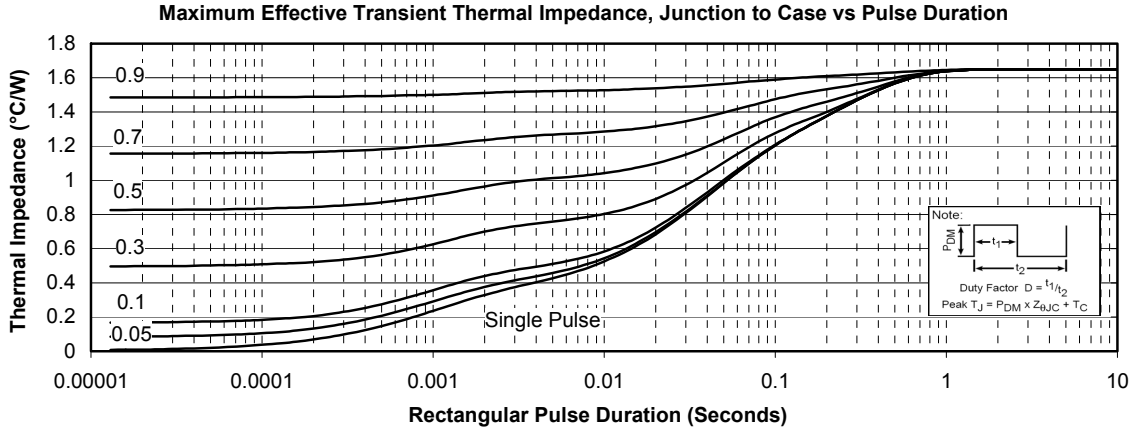
Gate Charge vs Gate to Source

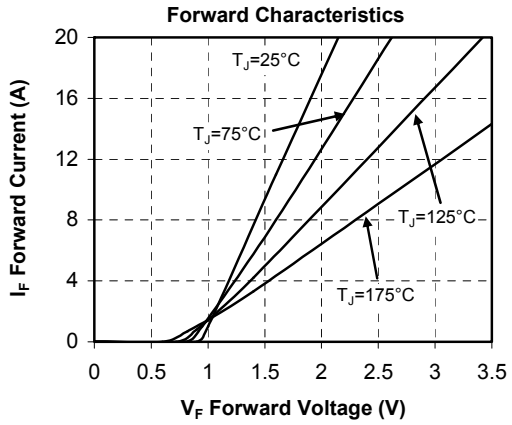


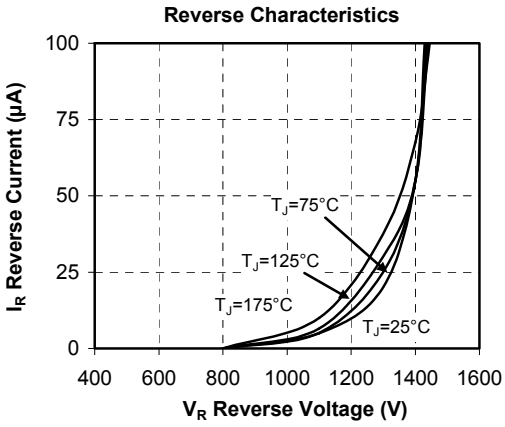
Capacitance vs Drain to Source Voltage

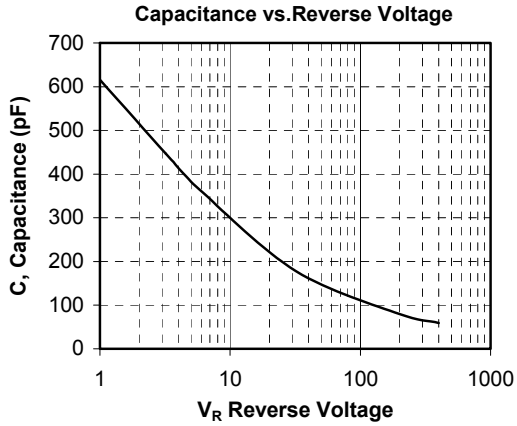


Typical SiC Diode Performance Curve









ISOTOP® is a registered trademark of ST Microelectronics NV

DISCLAIMER

The information contained in the document (unless it is publicly available on the Web without access restrictions) is PROPRIETARY AND CONFIDENTIAL information of Microsemi and cannot be copied, published, uploaded, posted, transmitted, distributed or disclosed or used without the express duly signed written consent of Microsemi. If the recipient of this document has entered into a disclosure agreement with Microsemi, then the terms of such Agreement will also apply. This document and the information contained herein may not be modified, by any person other than authorized personnel of Microsemi. No license under any patent, copyright, trade secret or other intellectual property right is granted to or conferred upon you by disclosure or delivery of the information, either expressly, by implication, inducement, estoppels or otherwise. Any license under such intellectual property rights must be approved by Microsemi in writing signed by an officer of Microsemi.

Microsemi reserves the right to change the configuration, functionality and performance of its products at anytime without any notice. This product has been subject to limited testing and should not be used in conjunction with life-support or other mission-critical equipment or applications. Microsemi assumes no liability whatsoever, and Microsemi disclaims any express or implied warranty, relating to sale and/or use of Microsemi products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright or other intellectual property right. Any performance specifications believed to be reliable but are not verified and customer or user must conduct and complete all performance and other testing of this product as well as any user or customers final application. User or customer shall not rely on any data and performance specifications or parameters provided by Microsemi. It is the customer's and user's responsibility to independently determine suitability of any Microsemi product and to test and verify the same. The information contained herein is provided "AS IS, WHERE IS" and with all faults, and the entire risk associated with such information is entirely with the User. Microsemi specifically disclaims any liability of any kind including for consequential, incidental and punitive damages as well as lost profit. The product is subject to other terms and conditions which can be located on the web at http://www.microsemi.com/legal/tnc.asp

Life Support Application

Seller's Products are not designed, intended, or authorized for use as components in systems intended for space, aviation, surgical implant into the body, in other applications intended to support or sustain life, or for any other application in which the failure of the Seller's Product could create a situation where personal injury, death or property damage or loss may occur (collectively "Life Support Applications").

Buyer agrees not to use Products in any Life Support Applications and to the extent it does it shall conduct extensive testing of the Product in such applications and further agrees to indemnify and hold Seller, and its officers, employees, subsidiaries, affiliates, agents, sales representatives and distributors harmless against all claims, costs, damages and expenses, and attorneys' fees and costs arising, directly or directly, out of any claims of personal injury, death, damage or otherwise associated with the use of the goods in Life Support Applications, even if such claim includes allegations that Seller was negligent regarding the design or manufacture of the goods.

Buyer must notify Seller in writing before using Seller's Products in Life Support Applications. Seller will study with Buyer alternative solutions to meet Buyer application specification based on Sellers sales conditions applicable for the new proposed specific part.